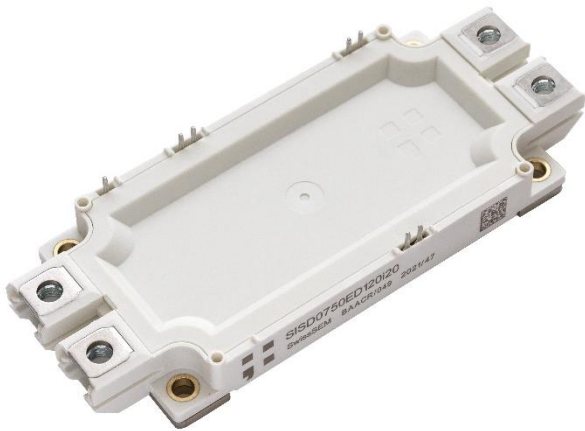


MATERIAL	ELEMENT	TOPOLOGY	CURRENT (A) or RDSon (mΩ)	MOD. TYPE	VOLTAGE (10 V)	CHIP GEN.	OPTION 1	OPTION 2	COMMENT
SC									SiC
Si									Silicon
	S								Switch
	D								Diode
		A							Single
		D							Dual
		H							H-Bridge
		L/U							Low/high-side chopper
		P							PIM
		S							Six-pack
		T							Three-level
			0800						Current per switch (example)
				ED					
				ST					
				TF					
				EP					
				FP					
				EVD					
				BEVD					
				HEEV					
				Txyz					 TO as example
				C					Chip
					120				Blocking voltage divided by 10 (example)
						lxx			IGBT generation
						dxx			Diode generation
						mxx			MOSFET generation
						sxx			Schottky diode generation
							_Axx		Product Version
							_Dxx		Different Diode rating
							_Exx		Automotive qualified
							_Fxx		Wafer front-side metallization



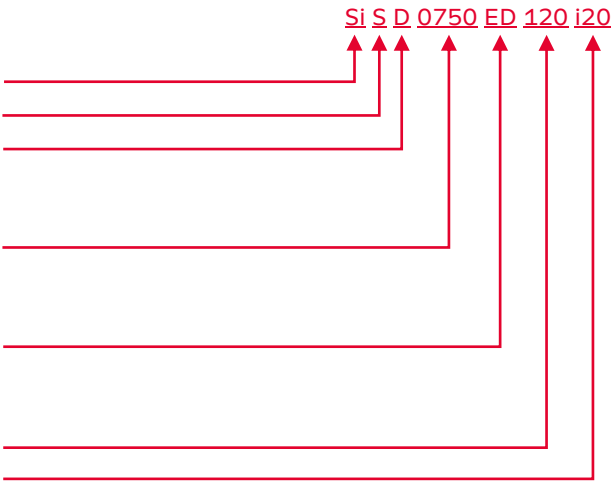
Silicon based semiconductor
Switch
Dual configuration
Current rating in ampere

- 0800
- 0750
- 0600
- 0450

ED-type module
Voltage class in volt divided by ten

- 170
- 120

/i20 chip generation



DATE
September 7th, 2022
February 6th, 2024
October 30th, 2025

AUTHOR
SM
SM
RSn

REMARK
Initial Version
Update with new product families
Update with new product families

AUTHOR
S.M.

CHECKED
VP PM and Application

RELEASED
PM Chip